

GJSD1802 NPN EPITAXIAL PLANAR SILICON TRANSISTOR

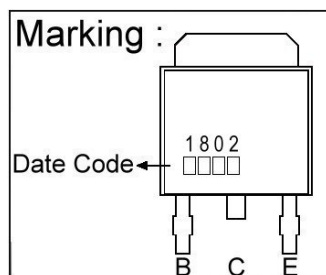
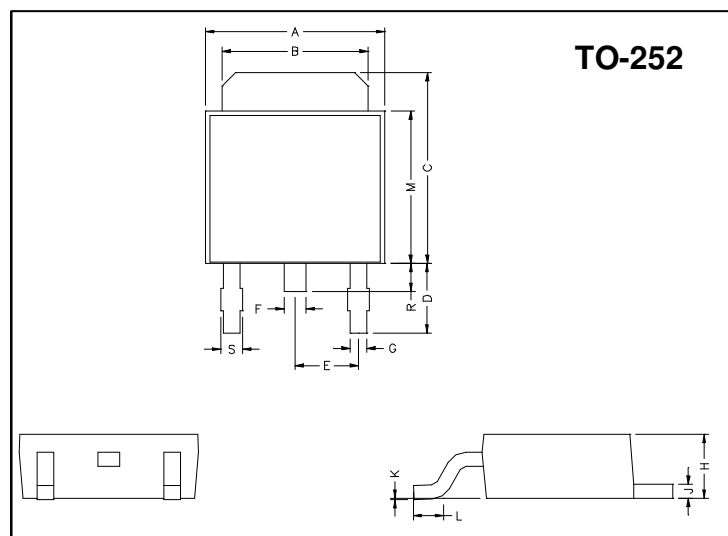
Description

The GJSD1802 applies to voltage regulators, relay drivers, lamp drivers, and electrical equipment.

Features

- *Adoption of FBET, MBIT processes
- *Large current capacity and wide ASO
- *Low collector-to-emitter saturation voltage
- *Fast switching speed

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VcBo	60	V
Collector to Emitter Voltage	VcEO	50	V
Emitter to Base Voltage	VEBO	6	V
Collector Current(DC)	Ic	3	A
Collector Current(Pulse)	IcP	6	A
Collector Dissipation	Pd	1	W
	Tc=25°C	20	W

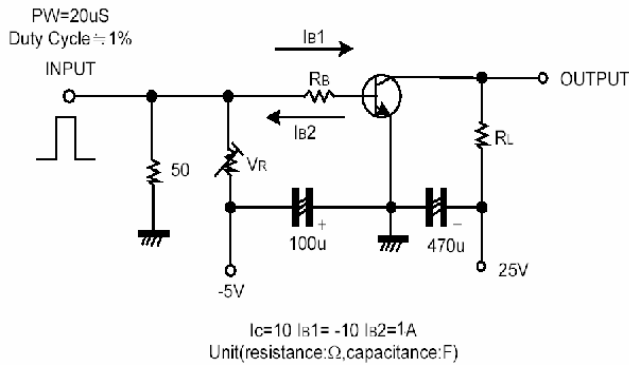
Electrical Characteristics (Ta = 25°C unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V(BR)CBO	60	-	-	V	Ic=10uA, IE=0
V(BR)CEO	50	-	-	V	Ic=1mA, RBE=∞
V(BR)EBO	6	-	-	V	IE=10uA, Ic=0
IcBO	-	-	1	μA	VcB=40V, IE=0
IEBO	-	-	1	μA	VEB=4V, Ic=0
VCE(sat)	-	0.19	0.5	V	Ic=2A, Ib=0.1A
VBE(sat)	-	0.94	1.2	V	Ic=2A, Ib=0.1A
hFE1	100	-	560		VCE=2V, Ic=0.1A
hFE2	35	-	-		VCE=2V, Ic=3A
fT	-	150	-	MHZ	VCE=10V, Ic=50mA
ton	-	70	-	ns	See test circuit
tstg	-	650	-	ns	See test circuit
tf	-	35	-	ns	See test circuit
Cob	-	25	-	pF	VcB=10V, f=1MHz

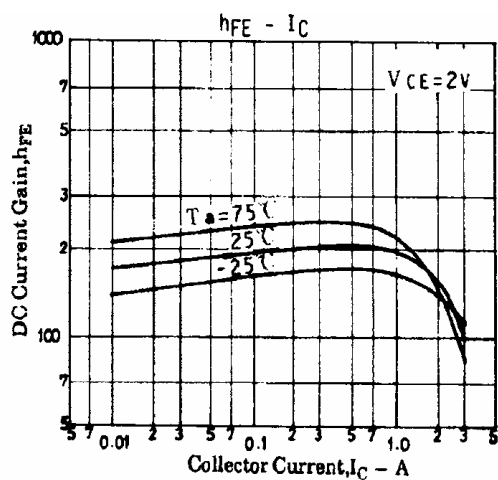
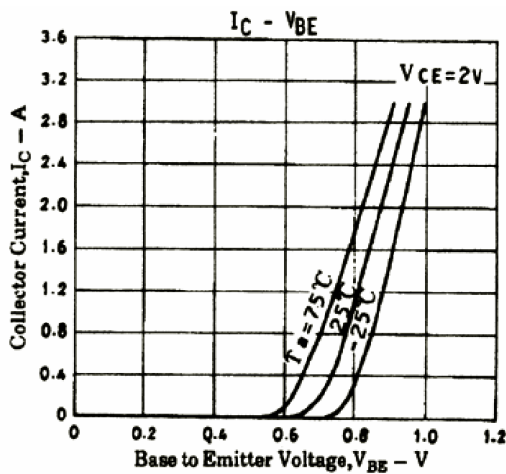
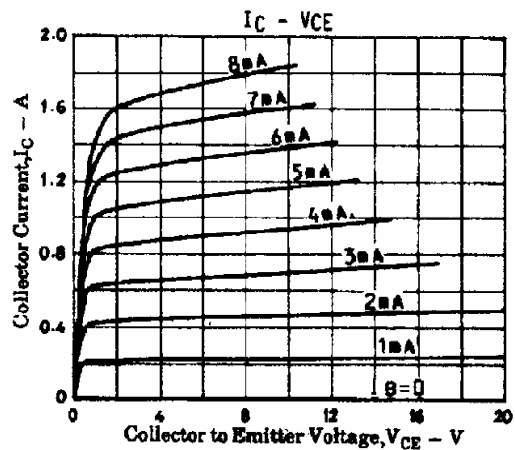
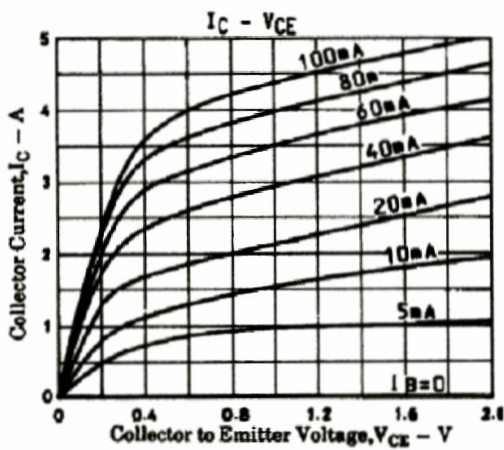
Classification Of hFE1

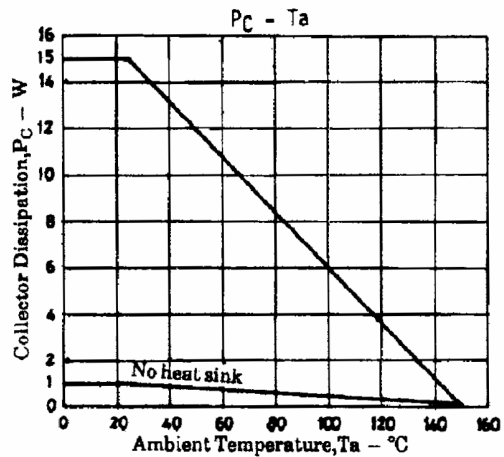
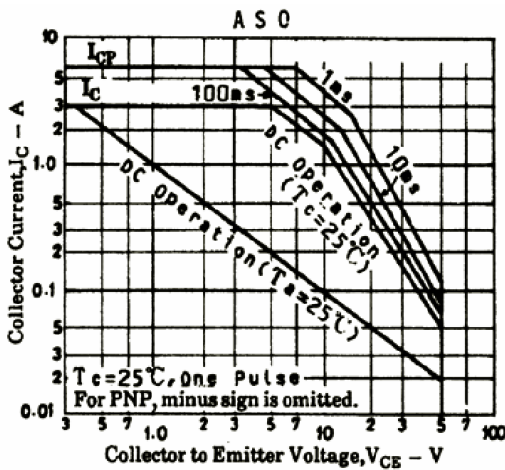
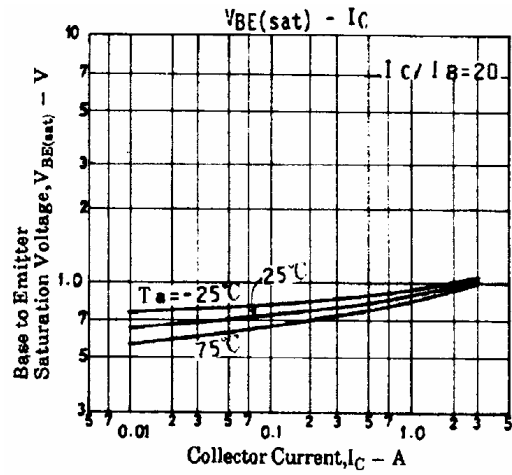
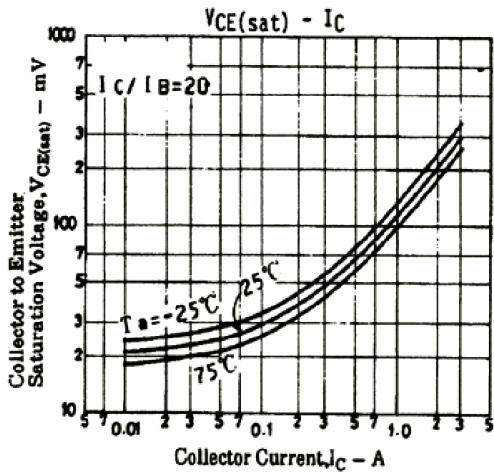
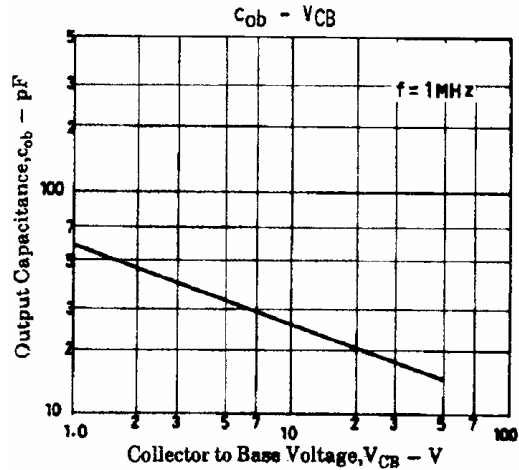
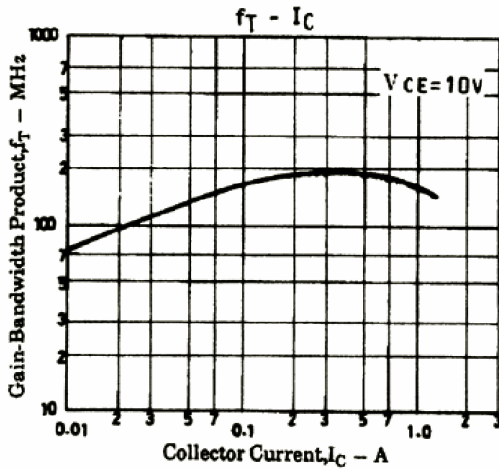
Rank	R	S	T	U
Range	100 ~ 200	140 ~ 280	200 ~ 400	280 ~ 560

Switching Time Test Circuit



Characteristics Curve





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